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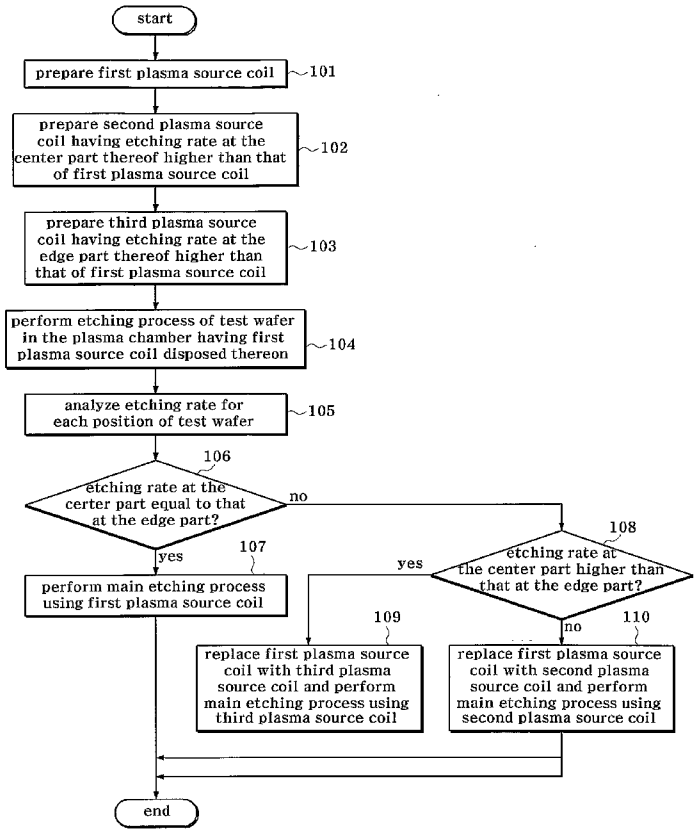
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(54) **Title:** METHOD FOR SETTING PLASMA CHAMBER HAVING AN ADAPTIVE PLASMA SOURCE, PLASMA ETCHING METHOD USING THE SAME AND MANUFACTURING METHOD FOR ADAPTIVE PLASMA SOURCE



(57) **Abstract:** Disclosed herein is a plasma chamber setting method for generating plasma in a plasma chamber. A plurality of plasma source coils, including a first plasma source coil, a second plasma source coil having an etching rate at the center part thereof higher than that of the first plasma source coil, and a third plasma source coil having an etching rate at the edge part thereof higher than that of the first plasma source coil, are prepared. The first plasma source coil is disposed on the plasma chamber, and a test wafer is etched. The etching rate for each position of the test wafer is analyzed, and first plasma source coil is replaced with the second plasma source coil or the third plasma source coil based on the analysis results.

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